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Nomenclature Used

E_g	Energy gap
$N(E)$	Density of states function
E_F	Fermi energy level
eV	Electron Volt
E_D	Donor energy level
E_A	Acceptor level
h	Planck's constant
F	frequency of the light
λ	wavelength
α	Absorption coefficient
E_{Fp}	Fermi energy level for P type material
E_{Fn}	Fermi energy level for n type material
V_D	Diode voltage
K	Boltzmann's constant
I_{diff}	Diffusion current
I_D	Diode Current
I_o	Dark saturation current
R_S	Series resistance
n	Ideality factor
V_{Br}	Breakdown voltage
R_{sh}	Shunt resistance
I_{ph}	Photo generated current
$J_{leakage}$	Leakage current density
$I_{leakage}$	Leakage Current
$A_{hotspot}$	Area of hotspot
I_{sc}	Short circuit current
V_{oc}	Open circuit voltage
P_{mpp}	Maximum output
I_{mpp}	Current at P_{mpp}
V_{mpp}	Voltage at P_{mpp}
FF	Fill factor
eta	Efficiency

P_{\max}	Maximum power
ΔI_{sc}	I_{sc} difference
ΔT	Temperature difference
R^2	Correlation factor